SN74LVCC4245A 具有可配置输出电压和三态输出的八路双电源总线收发器

1 特性

- 双向电压转换器
- A 端口的电压范围为 4.5V 至 5.5V，B 端口的电压范围为 2.7V 至 5.5V
- 控制输入 V_{IH} 和 V_{IL} 电平以 V_{CCA} 电压为基准
- 闩锁性能超过 250mA，符合 JESD 17 规范
- ESD 保护性能超过 JESD 22 规范要求
  - 2000V 人体放电模型 (A114-A)
  - 1000V 带电器件模型 (C101)

2 应用

- 电平转换
- 个人电子产品
- 工业
- 企业
- 电信

3 说明

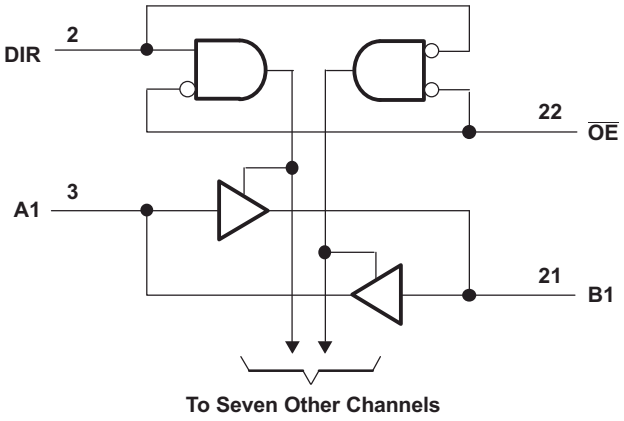
这款 8 位（八路）同相总线收发器采用两个独立的电源轨。A 端口 V_{CCA} 专用于接受 5V 电源电平，可配置的 B 端口（用于跟踪 V_{CCB}）接受 3V 至 5V 的电压。这样可实现从 3.3V 到 5V 的环境转换，反之亦然。

SN74LVCC4245A 器件旨在实现数据总线之间的异步通信。SN74LVCC4245A 器件根据方向控制 (DIR) 输入上的逻辑电平，将数据从 A 总线发送至 B 总线，或者将数据从 B 总线发送至 A 总线。输出使能 ($\overline{OE}$) 输入可用于禁用器件，这样可有效隔离总线。控制电路（DIR，$\overline{OE}$）由 V_{CCA} 供电。

封装信息(1)

器件型号	封装	封装尺寸（标称值）
SN74LVCC4245A	DB (SSOP, 24)	8.20mm × 5.30mm
	DW（SOIC，24）	15.40mm × 7.50mm
	NS（SOP，24）	15.00mm × 5.30mm
	PW（TSSOP，24）	7.80mm × 4.40mm

(1) 如需了解可用封装，请参阅数据表末尾的可订购产品附录。



逻辑图（正逻辑）

Table of Contents

4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision M (March 2005) to Revision N (December 2022)	Page
• 删除了订购信息	1
• 更新了整个文档中的表格、图和交叉参考的编号格式	1
• 添加了 *引脚配置和功能*、*详细说明*、*应用和实施*、*布局* 部分	1
• Added thermal values for PW package	5

5 Pin Configuration and Functions

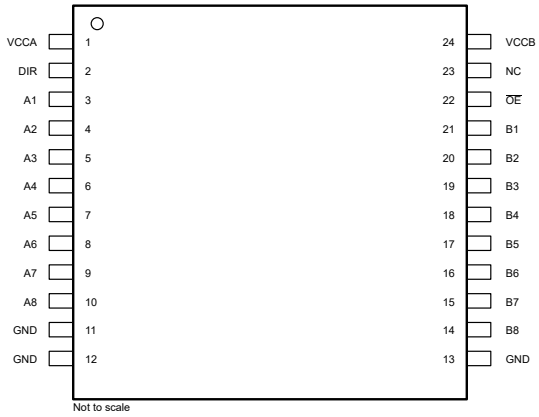


图 5-1. DB, DW, NS, or PW Package, SSOP, SOIC, SOP, or TSSOP (Top View)

表 5-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NAME	NO.		
V_{CCA}	1	—	A port power
DIR	2	I	Dir input
A1	3	I/O	A1 port
A2	4	I/O	A2 port
A3	5	I/O	A3 port
A4	6	I/O	A4 port
A5	7	I/O	A5 port
A6	8	I/O	A6 port
A7	9	I/O	A7 port
A8	10	I/O	A8 port
GND	11	—	Ground
GND	12	—	
GND	13	—	
B8	14	I/O	B8 port
B7	15	I/O	B7 port
B6	16	I/O	B6 port
B5	17	I/O	B5 port
B4	18	I/O	B4 port
B3	19	I/O	B3 port
B2	20	I/O	B2 port
B1	21	I/O	B1 port
$\overline{OE}$	22	I	Output Enable active low
NC	23	—	Unconnected
V_{CCB}	24	—	B port power

(1) Signal Types: I = Input, O = Output, I/O = Input or Output.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CCA} V_{CCB}	Supply voltage range		–0.5	6	V
V_I	Input voltage range(2)	I/O ports (A port)	–0.5	V_{CCA} + 0.5	V
		I/O ports (B port)	–0.5	V_{CCB} + 0.5	
		Except I/O ports	–0.5	V_{CCA} + 0.5	
V_O	Output voltage range(2)	A port	–0.5	V_{CCA} + 0.5	V
		B port	–0.5	V_{CCB} + 0.5	
I_{IK}	Input clamp current	V_I < 0		–50	mA
I_{OK}	Output clamp current	V_O < 0		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CCA}, V_{CCB}, or GND			±100	mA
θ_{JA}	Package thermal impedance(3)	DW package		46	°C/W
		NS package		65	
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) This value is limited to 6 V maximum.
(3) The package thermal impedance is calculated in accordance with JESD 51-7.

6.2 ESD Ratings

PARAMETER		DEFINITION	VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

(1)

		V_{CCA}	V_{CCB}	MIN	NOM	MAX	UNIT
V_{CCA}	Supply voltage			4.5	5	5.5	V
V_{CCB}	Supply voltage			2.7	3.3	5.5	V
V_{IHA}	High-level input voltage	4.5 V	2.7 V	2			V
			3.6 V	2			
		5.5 V	5.5 V	2			
V_{IHB}	High-level input voltage	4.5 V	2.7 V	2			V
			3.6 V	2			
		5.5 V	5.5 V	3.85			
V_{ILA}	Low-level input voltage	4.5 V	2.7 V			0.8	V
			3.6 V			0.8	
		5.5 V	5.5 V			0.8	
V_{ILB}	Low-level input voltage	4.5 V	2.7 V			0.8	V
			3.6 V			0.8	
		5.5 V	5.5 V			1.65	
V_{IH}	High-level input voltage (control pins) (referenced to V_{CCA})	4.5 V	2.7 V	2			V
			3.6 V	2			
		5.5 V	5.5 V	2			
V_{IL}	Low-level input voltage (control pins) (referenced to V_{CCA})	4.5 V	2.7 V			0.8	V
			3.6 V			0.8	
		5.5 V	5.5 V			0.8	
V_{IA}	Input voltage			0		V_{CCA}	V
V_{IB}	Input voltage			0		V_{CCB}	V
V_{OA}	Output voltage			0		V_{CCA}	V
V_{OB}	Output voltage			0		V_{CCB}	V
I_{OHA}	High-level output current	4.5 V	3 V			– 24	mA
I_{OHB}	High-level output current	4.5 V	2.7 V to 4.5 V			– 24	mA
I_{OLA}	Low-level output current	4.5 V	3 V			24	mA
I_{OLB}	Low-level output current	4.5 V	2.7 V to 4.5 V			24	mA
T_A	Operating free-air temperature			– 40		85	°C

(1) All unused inputs of the device must be held at the associated V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

6.4 Thermal Information

THERMAL METRIC(1)		SN74LVCC4245A		UNIT
		PW (TSSOP)	DB (SSOP)	
		24 PINS	24 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	100.6	90.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	44.7	51.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	55.8	49.7	°C/W
ψ_{JT}	Junction-to-top characterization parameter	6.8	18.8	°C/W

6.4 Thermal Information (continued)

THERMAL METRIC[1]		SN74LVCC4245A		UNIT
		PW (TSSOP)	DB (SSOP)	
		24 PINS	24 PINS	
ψ_{JB}	Junction-to-board characterization parameter	55.4	49.3	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC package thermal metrics* application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CCA}	V_{CCB}	MIN	TYP	MAX	UNIT
V_{OHA}		I_{OH} = –100 µA		4.5 V	3 V	4.4	4.49		V
		I_{OH} = –24 mA		4.5 V	3 V	3.76	4.25		
V_{OHB}		I_{OH} = –100 µA		4.5 V	3 V	2.9	2.99		V
		I_{OH} = –12 mA		4.5 V	2.7 V	2.2	2.5		
					3 V	2.46	2.85		
		I_{OH} = –24 mA		4.5 V	2.7 V	2.1	2.3		
					3 V	2.25	2.65		
					4.5 V	3.76	4.25		
V_{OLA}		I_{OL} = 100 µA		4.5 V	3 V			0.1	V
		I_{OL} = 24 mA		4.5 V	3 V		0.21	0.44	
V_{OLB}		I_{OL} = 100 µA		4.5 V	3 V			0.1	V
		I_{OL} = 12 mA		4.5 V	2.7 V		0.11	0.44	
		I_{OL} = 24 mA		4.5 V	2.7 V		0.22	0.5	
					3 V		0.21	0.44	
					4.5 V		0.18	0.44	
I_I	Control inputs	V_I = V_{CCA} or GND		5.5 V	3.6 V		±0.1	±1	µA
					5.5 V		±0.1	±1	
I_{OZ} [1]	A or B ports	V_O = $V_{CCA/B}$ or GND,	V_I = V_{IL} or V_{IH}	5.5 V	3.6 V		±0.5	±5	µA
I_{CCA}	B to A	A_n = V_{CC} or GND		5.5 V	Open		8	80	µA
		I_O (A port) = 0,	B_n = V_{CCB} or GND	5.5 V	3.6 V		8	80	
					5.5 V		8	80	
I_{CCB}	A to B	A_n = V_{CCA} or GND,	I_O (B port) = 0	5.5 V	3.6 V		5	50	µA
					5.5 V		8	80	
ΔI_{CCA} [2]	A port	V_I = V_{CCA} – 2.1 V, Other inputs at V_{CCA} or GND, $\overline{OE}$ at GND and DIR at V_{CCA}		5.5 V	5.5 V		1.35	1.5	mA
	$\overline{OE}$	V_I = V_{CCA} – 2.1 V, Other inputs at V_{CCA} or GND, DIR at V_{CCA} or GND		5.5 V	5.5 V		1	1.5	
	DIR	V_I = V_{CCA} – 2.1 V, Other inputs at V_{CCA} or GND, $\overline{OE}$ at V_{CCA} or GND		5.5 V	3.6 V		1	1.5	
ΔI_{CCB} [2]	B port	V_I = V_{CCB} – 0.6 V, Other inputs at V_{CCB} or GND, $\overline{OE}$ at GND and DIR at GND		5.5 V	3.6 V		0.35	0.5	mA
C_i	Control inputs	V_I = V_{CCA} or GND		Open	Open		5		pF
C_{io}	A or B ports	V_O = $V_{CCA/B}$ or GND		5 V	3.3 V		11		pF

(1) For I/O ports, the parameter I_{OZ} includes the input leakage current.
(2) This is the increase in supply current for each input that is at one of the specified TTL voltage levels, rather than 0 V or the associated V_{CC}.

6.6 Switching Characteristics

over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see 图 8-1 through 图 11-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCA} = 5 V ± 0.5 V, V_{CCB} = 5 V ± 0.5 V		V_{CCA} = 5 V ± 0.5 V, V_{CCB} = 2.7 V to 3.6 V		UNIT
			MIN	MAX	MIN	MAX	
t_{PHL}	A	B	1	7.1	1	7	ns
t_{PLH}			1	6	1	7	
t_{PHL}	B	A	1	6.8	1	6.2	ns
t_{PLH}			1	6.1	1	5.3	
t_{PZL}	$\overline{OE}$	A	1	9	1	9	ns
t_{PZH}			1	8.3	1	8	
t_{PZL}	$\overline{OE}$	B	1	8.2	1	10	ns
t_{PZH}			1	8.1	1	10.2	
t_{PLZ}	$\overline{OE}$	A	1	4.7	1	5.2	ns
t_{PHZ}			1	4.9	1	5.2	
t_{PLZ}	$\overline{OE}$	B	1	5.4	1	5.9	ns
t_{PHZ}			1	6.3	1	7.4	

6.7 Operating Characteristics

V_{CCA} = 5 V, V_{CCB} = 3.3 V, T_A = 25°C

PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 0, f = 10 MHz	20	pF
		Outputs disabled		6.5	

6.8 Typical Characteristics

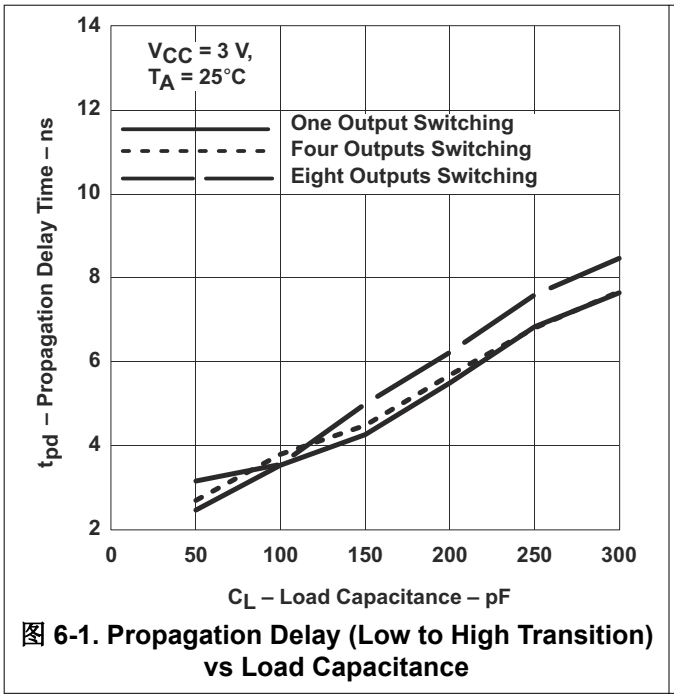


图 6-1. Propagation Delay (Low to High Transition) vs Load Capacitance

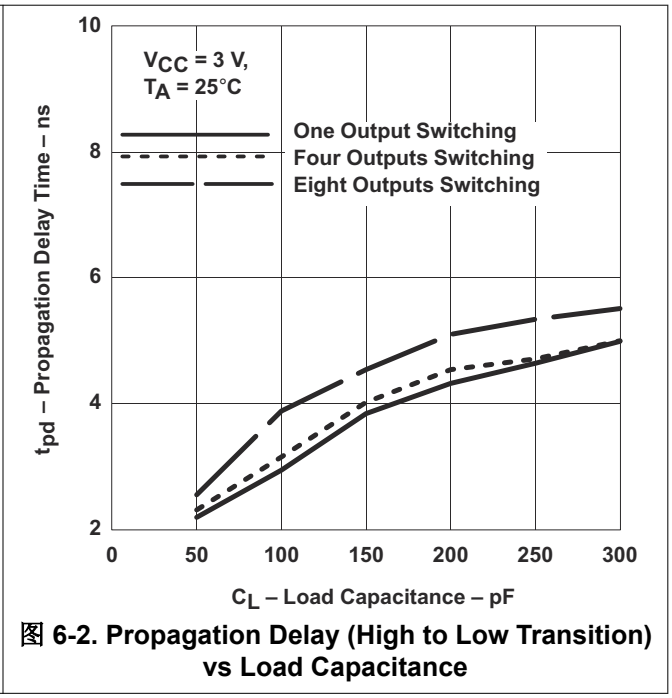


图 6-2. Propagation Delay (High to Low Transition) vs Load Capacitance

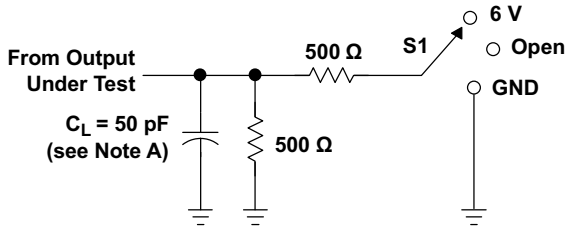
7 Power-Up Consideration

TI level-translation devices offer an opportunity for successful mixed-voltage signal design. A proper power-up sequence always should be followed to avoid excessive supply current, bus contention, oscillations, or other anomalies caused by improperly biased device pins. Take these precautions to guard against such power-up problems:

1. Connect ground before any supply voltage is applied.
2. Power up the control side of the device (V_{CCA} for all four of these devices).
3. Tie $\overline{OE}$ to V_{CCA} with a pull up resistor so that it ramps with V_{CCA}.
4. Depending on the direction of the data path, DIR can be high or low. If DIR high is needed (A data to B bus), then ramp it with V_{CCA}. Otherwise, keep DIR low.

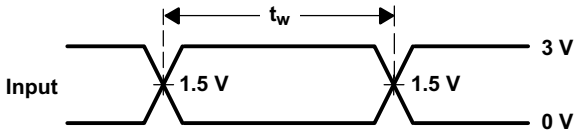
For more information, refer to the *Voltage-Level-Translation Devices* application note.

8 Parameter Measurement Information For A to B V_{CCA} = 4.5 V to 5.5 V and V_{CCB} = 2.7 V to 3.6 V

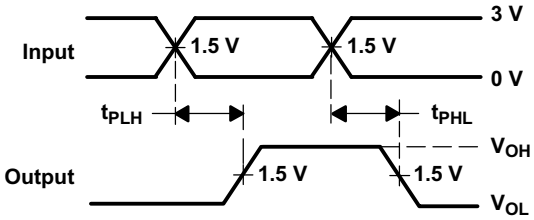


LOAD CIRCUIT

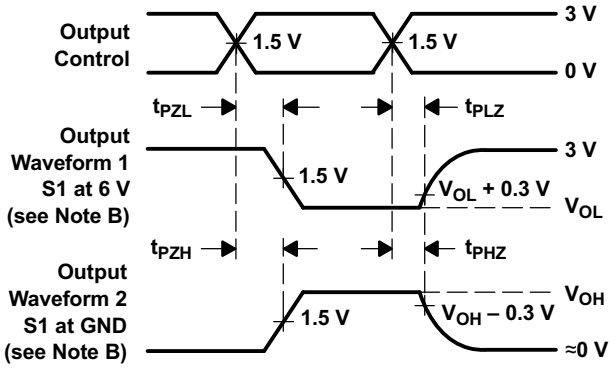
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
NONINVERTING OUTPUTS

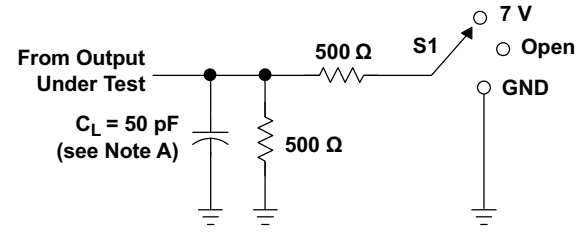


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤10 MHz, Z_O = 50 Ω, t_r ≤2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time, with one transition per measurement.
E. All parameters and waveforms are not applicable to all devices.

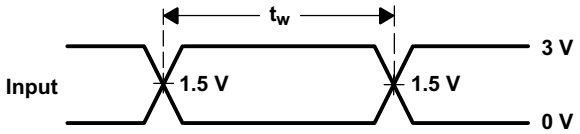
图 8-1. Load Circuit and Voltage Waveforms

9 Parameter Measurement Information For A to B
V_{CCA} = 4.5 V to 5.5 V and V_{CCB} = 3.6 V to 5.5 V

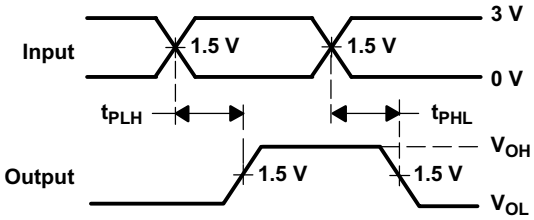


LOAD CIRCUIT

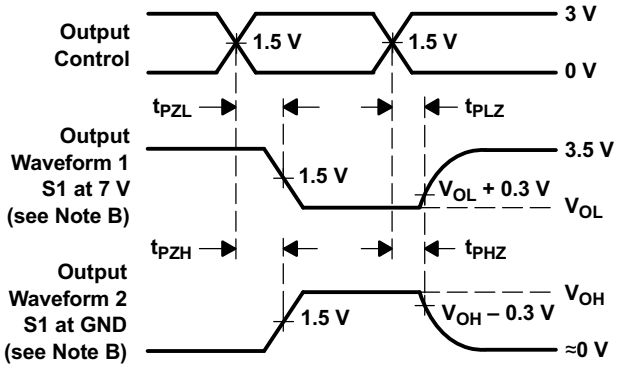
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
NONINVERTING OUTPUTS

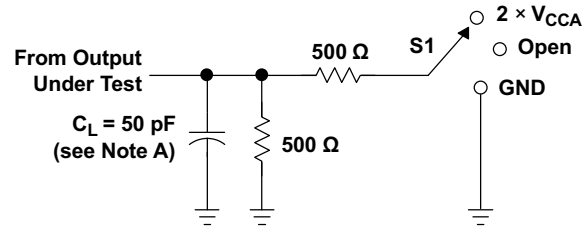


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time, with one transition per measurement.
E. All parameters and waveforms are not applicable to all devices.

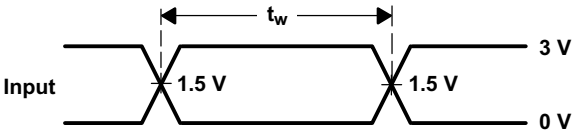
图 9-1. Load Circuit and Voltage Waveforms

10 Parameter Measurement Information For B to A V_{CCA} = 4.5 V to 5.5 V and V_{CCB} = 2.7 V to 3.6 V

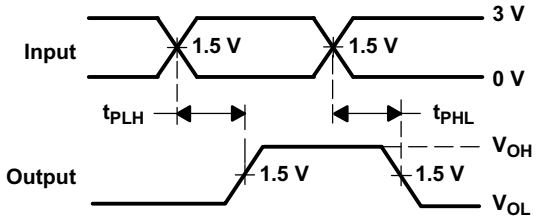


LOAD CIRCUIT

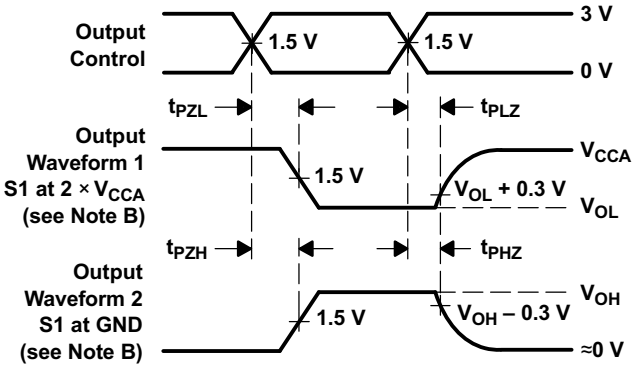
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	2 × V_{CCA}
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
NONINVERTING OUTPUTS

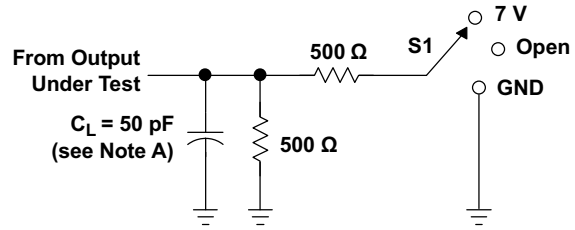


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time, with one transition per measurement.
E. All parameters and waveforms are not applicable to all devices.

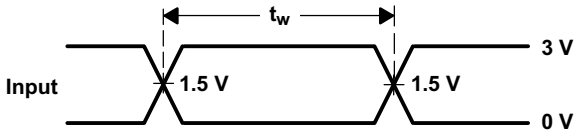
图 10-1. Load Circuit and Voltage Waveforms

11 Parameter Measurement Information For B to A V_{CCA} = 4.5 V to 5.5 V and V_{CCB} = 3.6 V to 5.5 V

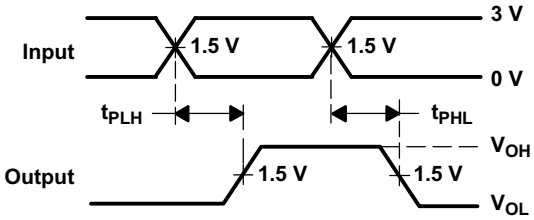


LOAD CIRCUIT

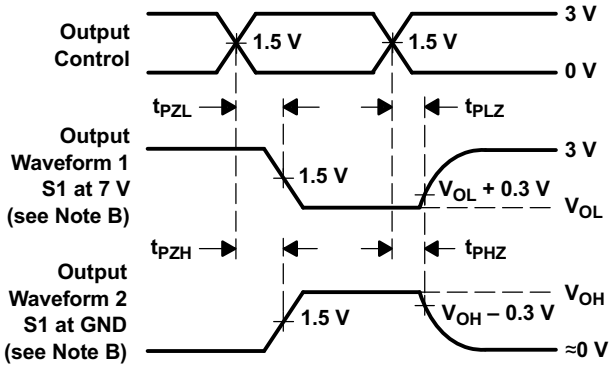
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time, with one transition per measurement.
E. All parameters and waveforms are not applicable to all devices.

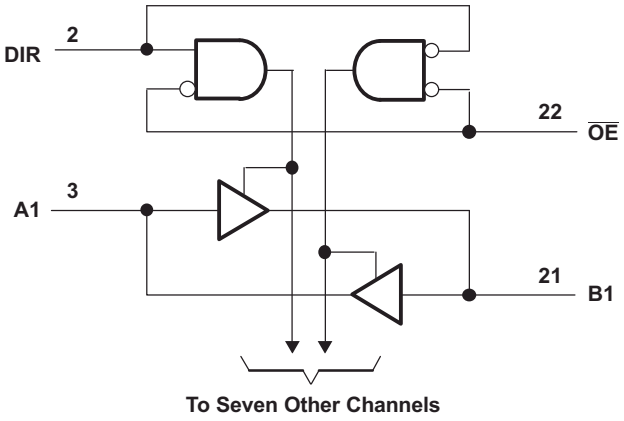
图 11-1. Load Circuit and Voltage Waveforms

12 Detailed Description

12.1 Overview

SN74LVCC4245A is an 8-bit (octal) noninverting bus transceiver contains two separate supply rails; B port has V_{CCB}, which is set at 3.3 V, and A port has V_{CCA}, which is set at 5 V. This allows for translation from a 3.3-V to a 5-V environment, and vice versa, designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so the buses are effectively isolated. The control circuitry (DIR, $\overline{OE}$) is powered by V_{CCA}.

12.2 Functional Block Diagram



12.3 Feature Description

- 24 mA drive at 3-V supply
  - Good for heavier loads and longer traces
- Low V_{IH}
  - Allows 3.3-V to 5-V translation

12.4 Device Functional Modes

表 12-1. Function Table (Each Transceiver)

INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

13 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

13.1 Application Information

The SN74LVCC4245A device pinout allows the designer to switch to a normal all-3.3-V or all-5-V 20-pin '245 device without board re-layout. The designer uses the data paths for pins 2 – 11 and 14 – 23 of the SN74LVC4245A to align with the conventional SN74LVC4245A device's pinout. SN74LVCC4245A is a high drive CMOS device that can be used for a multitude of bus interface type applications where output drive or PCB trace length is a concern.

13.2 Typical Application

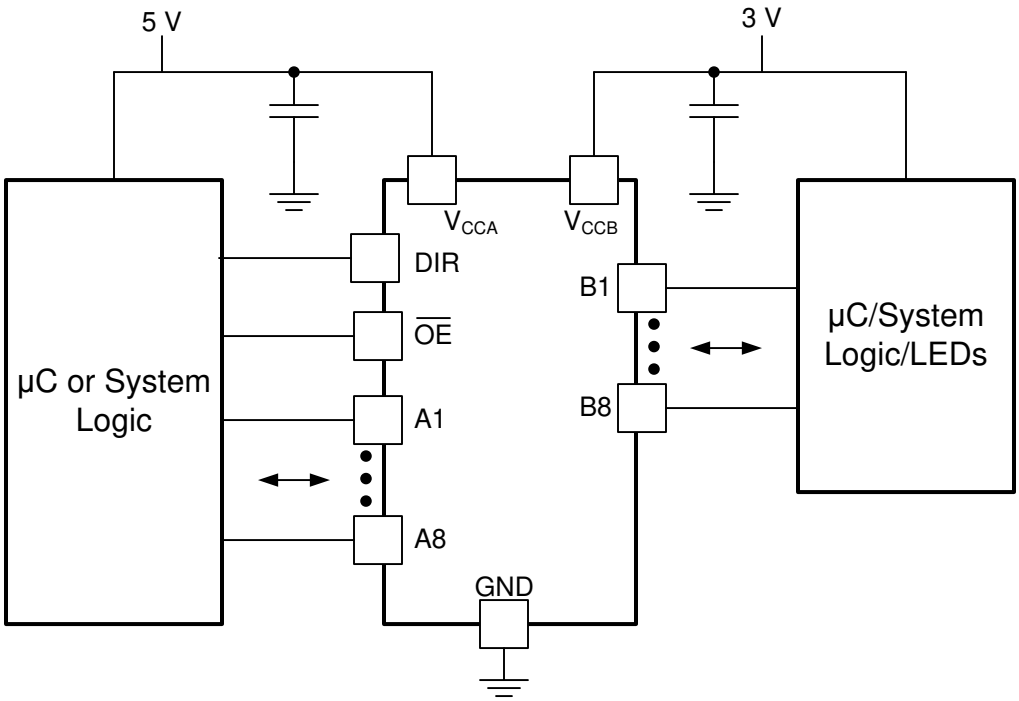


图 13-1. Typical Application Schematic

13.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

13.2.2 Detailed Design Procedure

1. Recommended Input Conditions:
   - For rise time and fall time specifcations, see ($\Delta t/\Delta V$) in the 节 6.3 table.
   - For specified high and low levels, see (V_{IH} and V_{IL}) in the 节 6.3 table.
2. Recommend Output Conditions:
   - Load currents should not exceed (I_O max) per output and should not exceed (Continuous current through V_{CC} or GND) total current for the part. These limits are located in the 节 6.1 table.
   - Outputs should not be pulled above V_{CC}.
   - Series resistors on the output may be used if the user desires to slow the output edge signal or limit the output current.

13.2.3 Application Curves

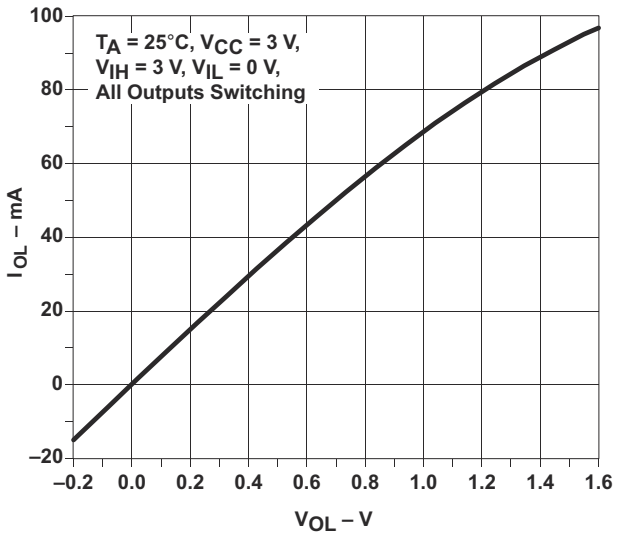


图 13-2. Output Drive Current (I_{OL}) vs LOW-level Output Voltage (V_{OL})

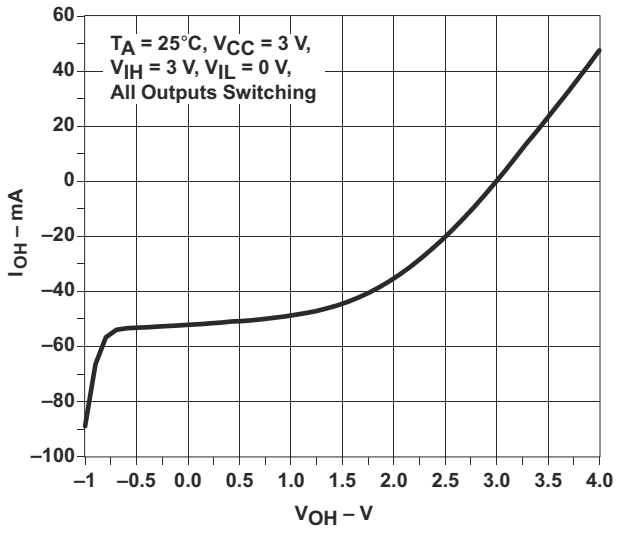


图 13-3. Output Drive Current (I_{OH}) vs HIGH-level Output Voltage (V_{OH})

14 Power Supply Recommendations

TI level-translation devices offer an opportunity for successful mixed-voltage signal design. A proper power-up sequence always should be followed to avoid excessive supply current, bus contention, oscillations, or other anomalies caused by improperly biased device terminals. Take these precautions to guard against such power-up problems:

1. Connect ground before any supply voltage is applied.
2. Power up the control side of the device (V_{CCA} for all four of these devices).
3. Tie $\overline{OE}$ to V_{CCA} with a pullup resistor so that it ramps with V_{CCA}.
4. Depending on the direction of the data path, DIR can be high or low. If DIR high is needed (A data to B bus), then ramp it with V_{CCA}. Otherwise, keep DIR low.

15 Layout

15.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in 图 15-1 are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC}, whichever makes more sense or is more convenient.

15.2 Layout Example

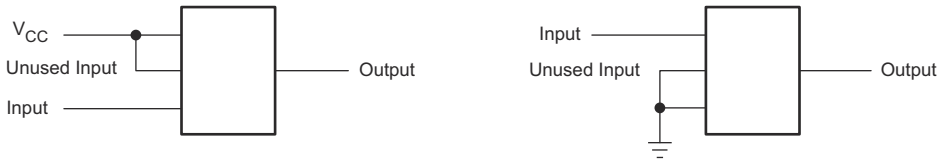


图 15-1. Layout Diagram

16 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

16.1 Documentation Support

16.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *Voltage-Level-Translation Devices* application note

16.2 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 *订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

16.3 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

16.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
所有商标均为其各自所有者的财产。

16.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

16.6 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

17 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74LVCC4245ADBR	Active	Production	SSOP (DB) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A
SN74LVCC4245ADBR.B	Active	Production	SSOP (DB) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A
SN74LVCC4245ADBRG4	Active	Production	SSOP (DB) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A
SN74LVCC4245ADBRG4.B	Active	Production	SSOP (DB) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A
SN74LVCC4245ADW	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCC4245A
SN74LVCC4245ADW.B	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCC4245A
SN74LVCC4245ADWE4	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCC4245A
SN74LVCC4245ADWR	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 85	LVCC4245A
SN74LVCC4245ADWR.B	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCC4245A
SN74LVCC4245ADWRG4	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCC4245A
SN74LVCC4245ADWRG4.B	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCC4245A
SN74LVCC4245ANSR	Active	Production	SOP (NS) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCC4245A
SN74LVCC4245ANSR.B	Active	Production	SOP (NS) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCC4245A
SN74LVCC4245ANSRG4	Active	Production	SOP (NS) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCC4245A
SN74LVCC4245ANSRG4.B	Active	Production	SOP (NS) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVCC4245A
SN74LVCC4245APW	Active	Production	TSSOP (PW) | 24	60 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A
SN74LVCC4245APW.B	Active	Production	TSSOP (PW) | 24	60 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A
SN74LVCC4245APWR	Active	Production	TSSOP (PW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A
SN74LVCC4245APWR.A	Active	Production	TSSOP (PW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A
SN74LVCC4245APWRE4	Active	Production	TSSOP (PW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A
SN74LVCC4245APWRG4	Active	Production	TSSOP (PW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A
SN74LVCC4245APWT	Active	Production	TSSOP (PW) | 24	250 | SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A
SN74LVCC4245APWT.B	Active	Production	TSSOP (PW) | 24	250 | SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A
SN74LVCC4245APWTE4	Active	Production	TSSOP (PW) | 24	250 | SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LG245A

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

OTHER QUALIFIED VERSIONS OF SN74LVCC4245A :

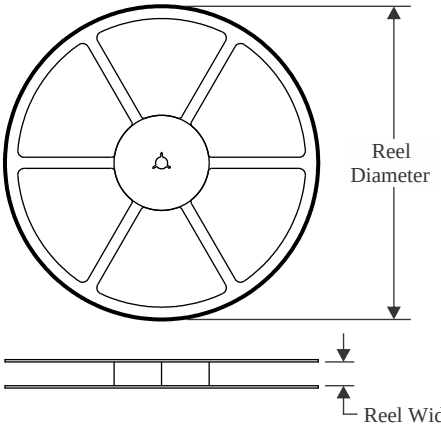
- Enhanced Product : SN74LVCC4245A-EP

NOTE: Qualified Version Definitions:

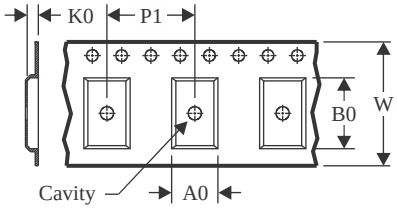
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION

REEL DIMENSIONS

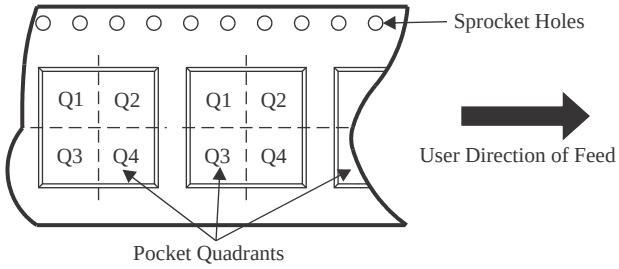


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

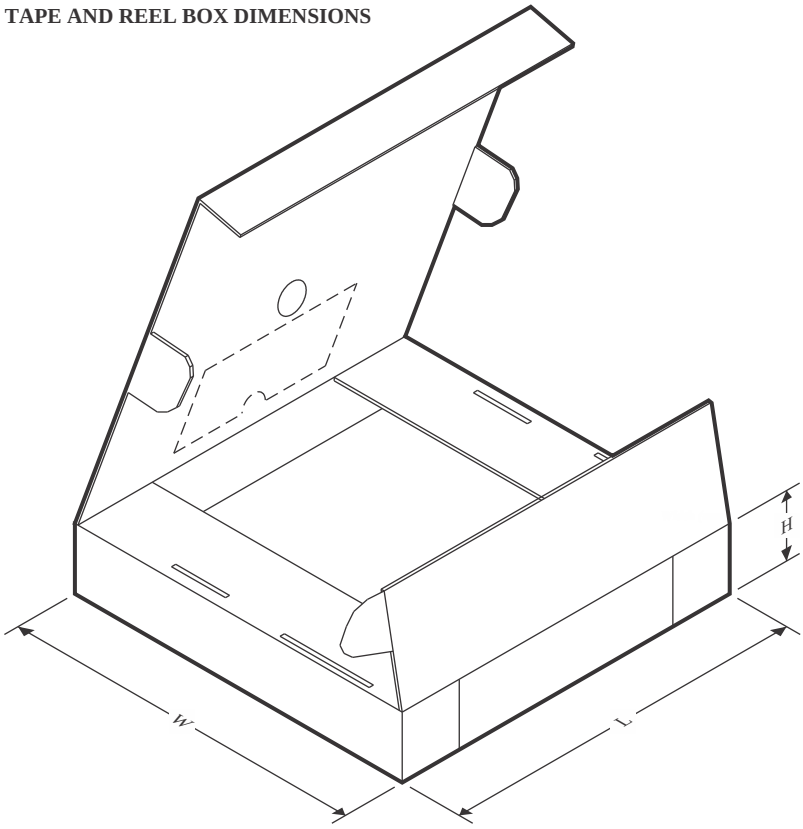
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVCC4245ADBR	SSOP	DB	24	2000	330.0	16.4	8.2	8.8	2.5	12.0	16.0	Q1
SN74LVCC4245ADBRG4	SSOP	DB	24	2000	330.0	16.4	8.2	8.8	2.5	12.0	16.0	Q1
SN74LVCC4245ADWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
SN74LVCC4245ADWRG4	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
SN74LVCC4245APWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
SN74LVCC4245APWT	TSSOP	PW	24	250	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1

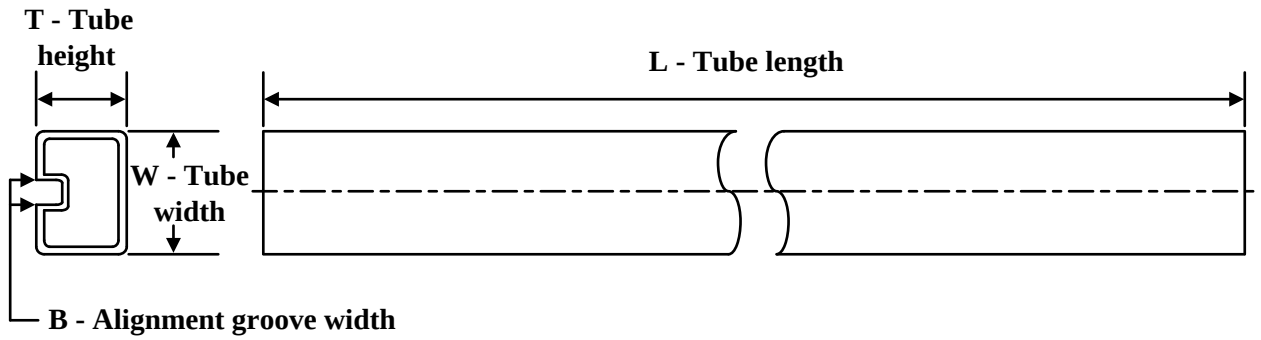
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVCC4245ADBR	SSOP	DB	24	2000	353.0	353.0	32.0
SN74LVCC4245ADBRG4	SSOP	DB	24	2000	353.0	353.0	32.0
SN74LVCC4245ADWR	SOIC	DW	24	2000	350.0	350.0	43.0
SN74LVCC4245ADWRG4	SOIC	DW	24	2000	350.0	350.0	43.0
SN74LVCC4245APWR	TSSOP	PW	24	2000	353.0	353.0	32.0
SN74LVCC4245APWT	TSSOP	PW	24	250	353.0	353.0	32.0

TUBE



*All dimensions are nominal

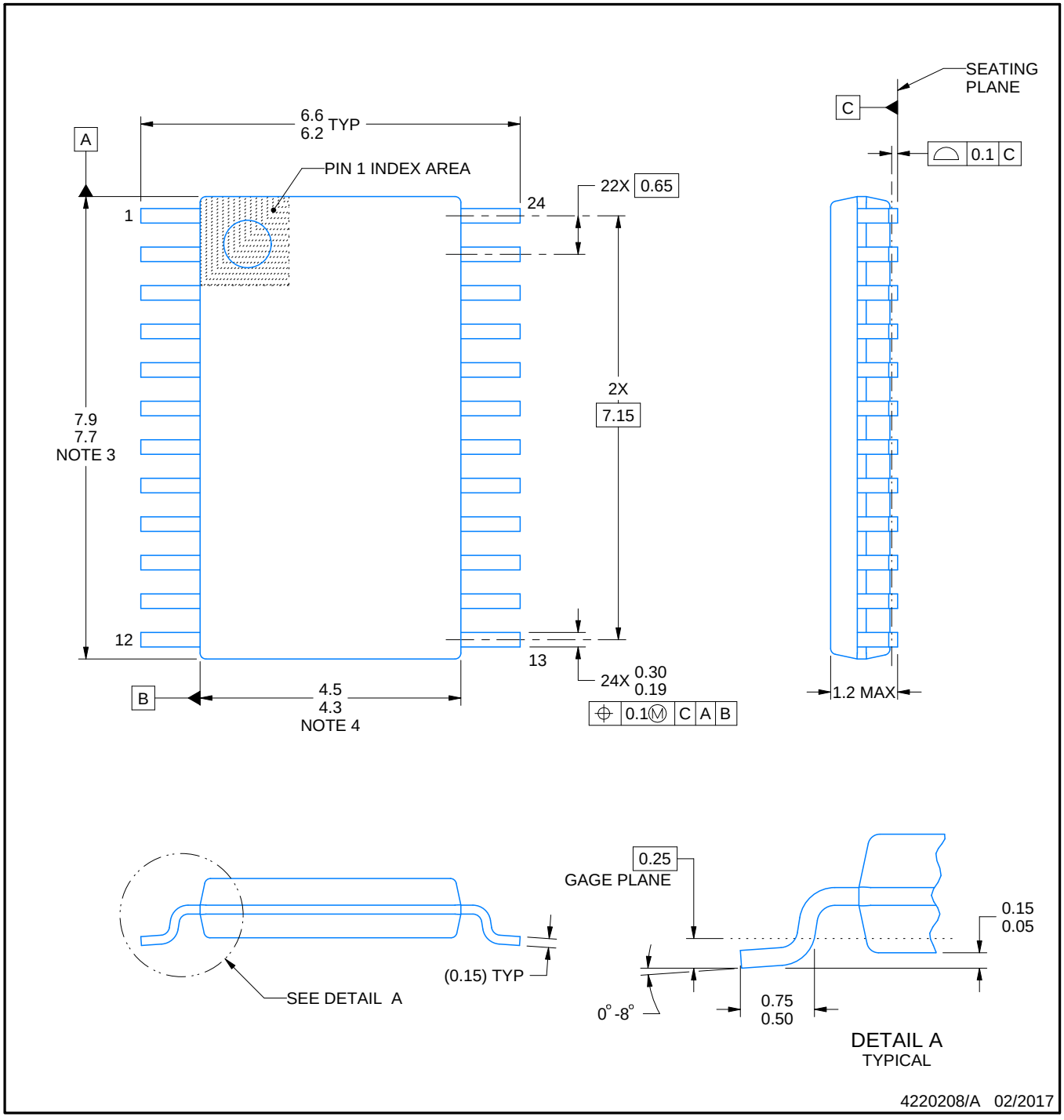
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74LVCC4245ADW	DW	SOIC	24	25	506.98	12.7	4826	6.6
SN74LVCC4245ADW.B	DW	SOIC	24	25	506.98	12.7	4826	6.6
SN74LVCC4245ADWE4	DW	SOIC	24	25	506.98	12.7	4826	6.6
SN74LVCC4245APW	PW	TSSOP	24	60	530	10.2	3600	3.5
SN74LVCC4245APW.B	PW	TSSOP	24	60	530	10.2	3600	3.5

PACKAGE OUTLINE

PW0024A

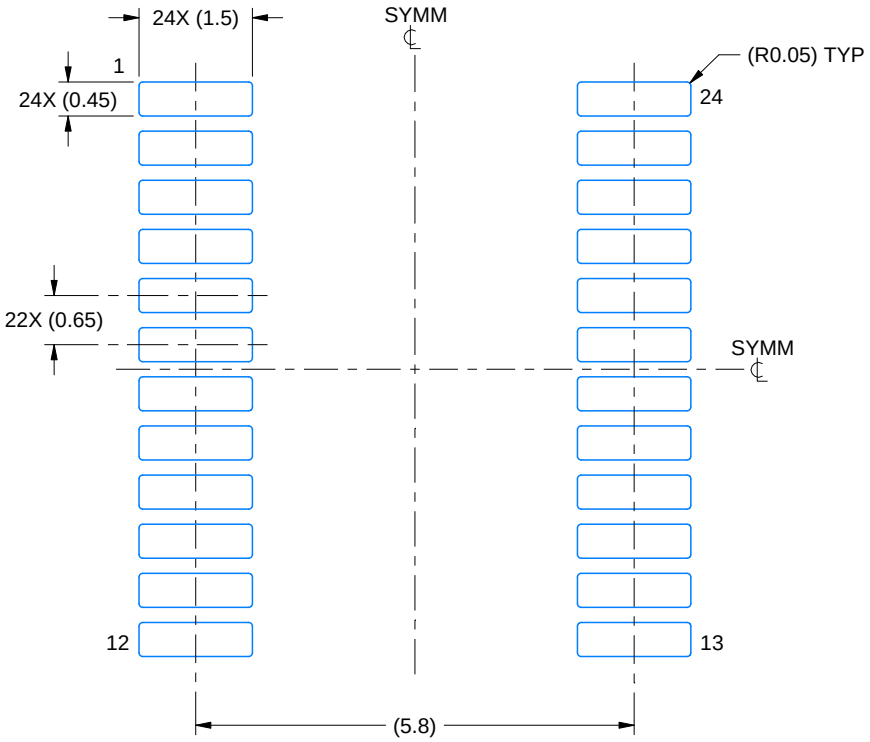
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

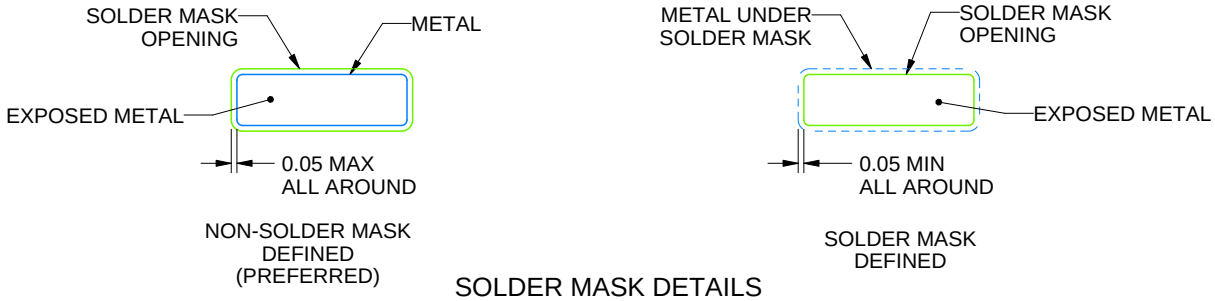


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

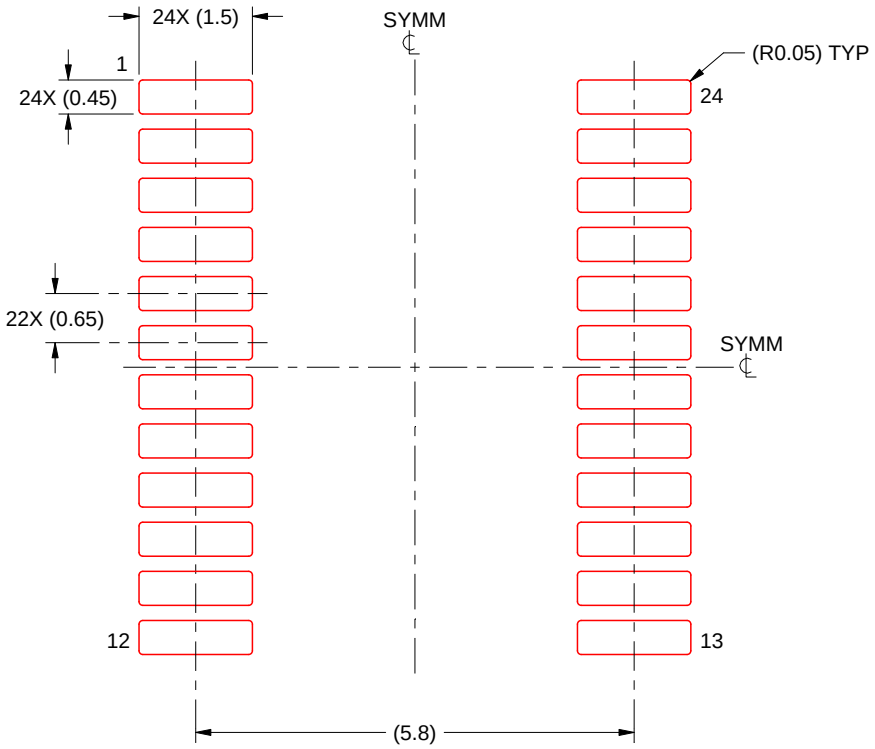


SOLDER MASK DETAILS

4220208/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220208/A 02/2017

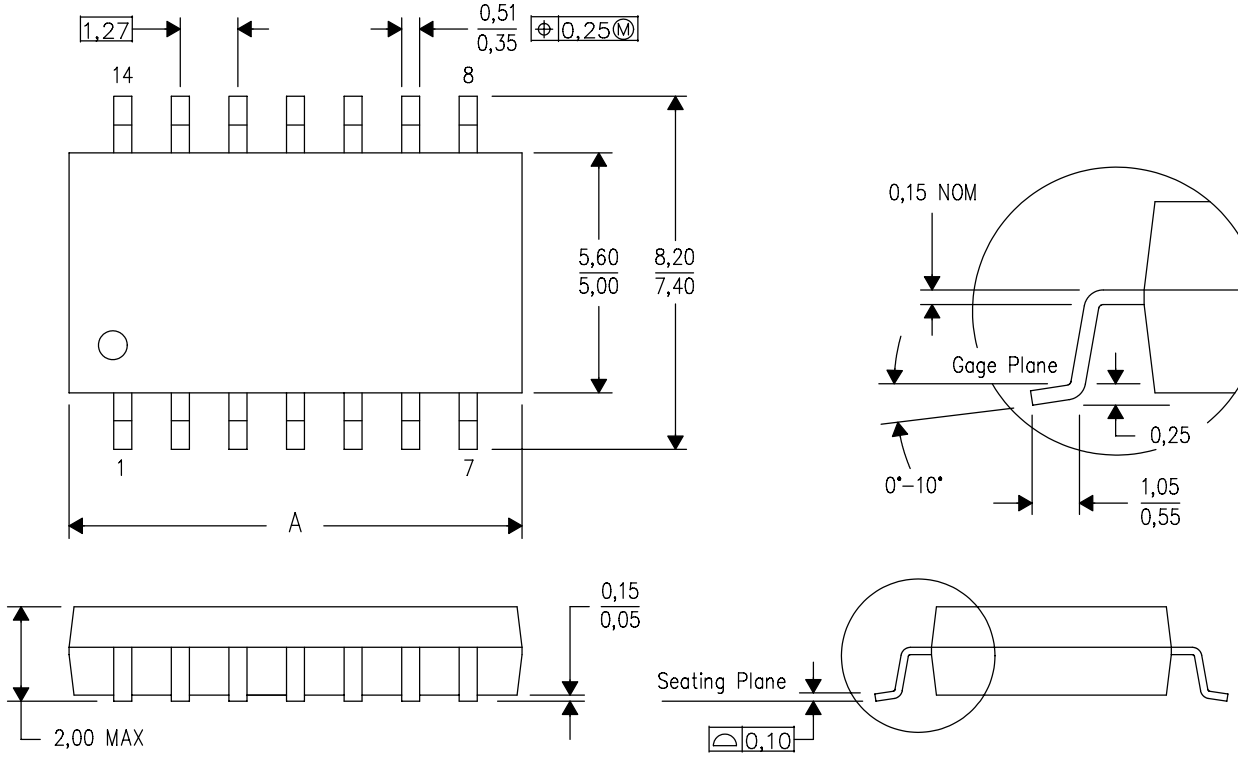
NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

MECHANICAL DATA

NS (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14-PINS SHOWN

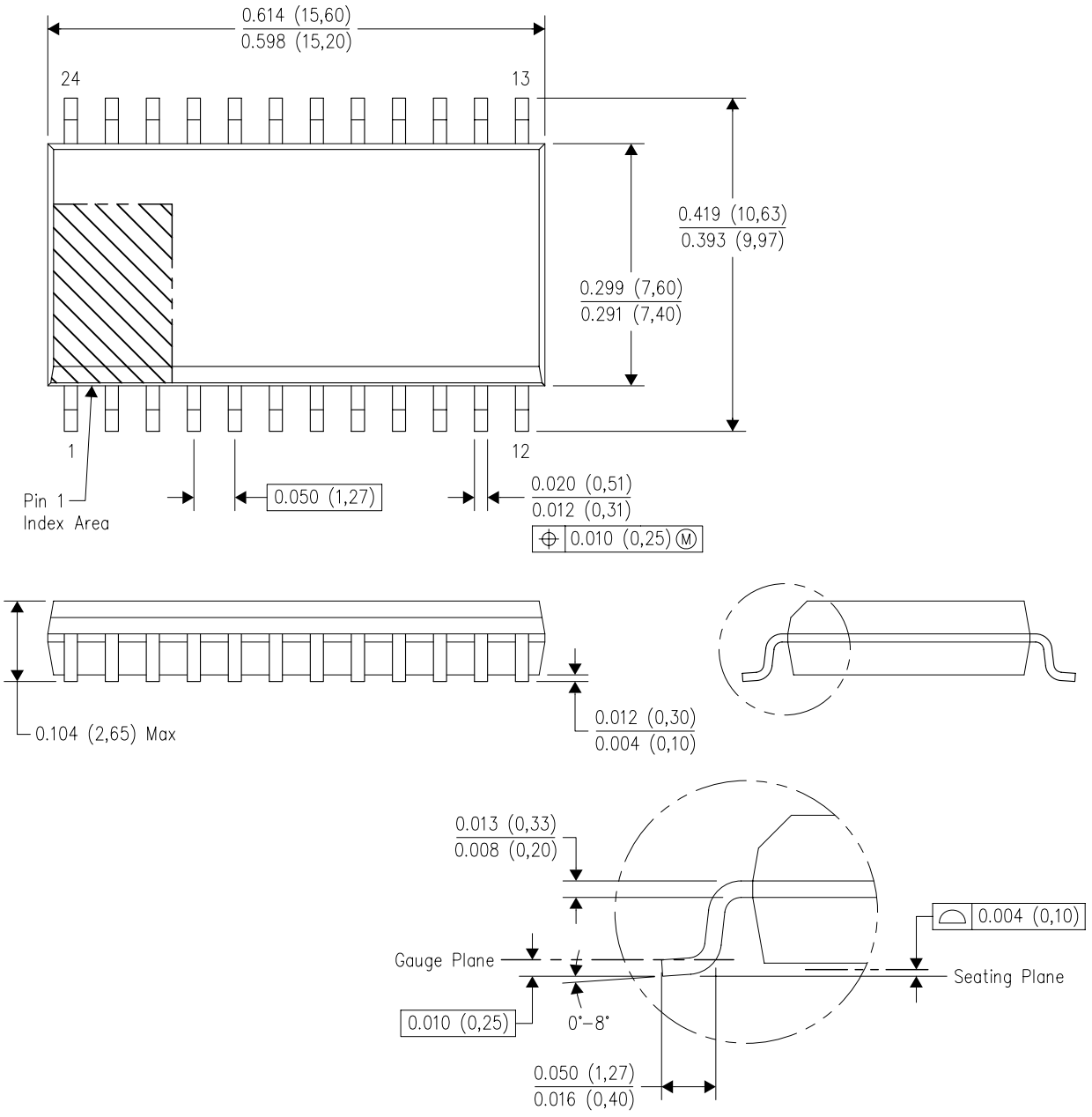


DIM \ PINS **	14	16	20	24
A MAX	10,50	10,50	12,90	15,30
A MIN	9,90	9,90	12,30	14,70

4040062/C 03/03

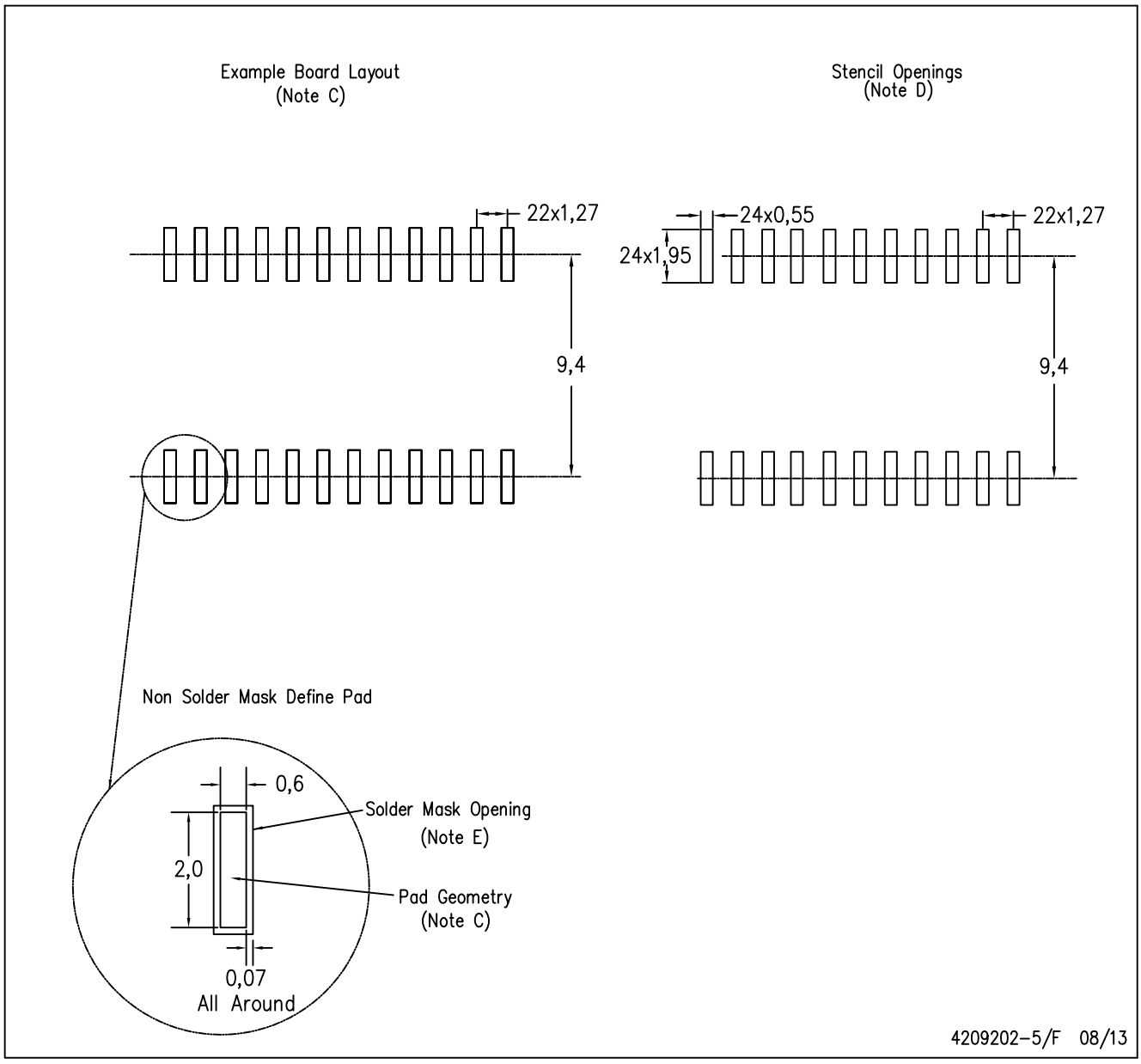
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

DW (R–PDSO–G24) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS–013 variation AD.

DW (R–PDSO–G24) PLASTIC SMALL OUTLINE

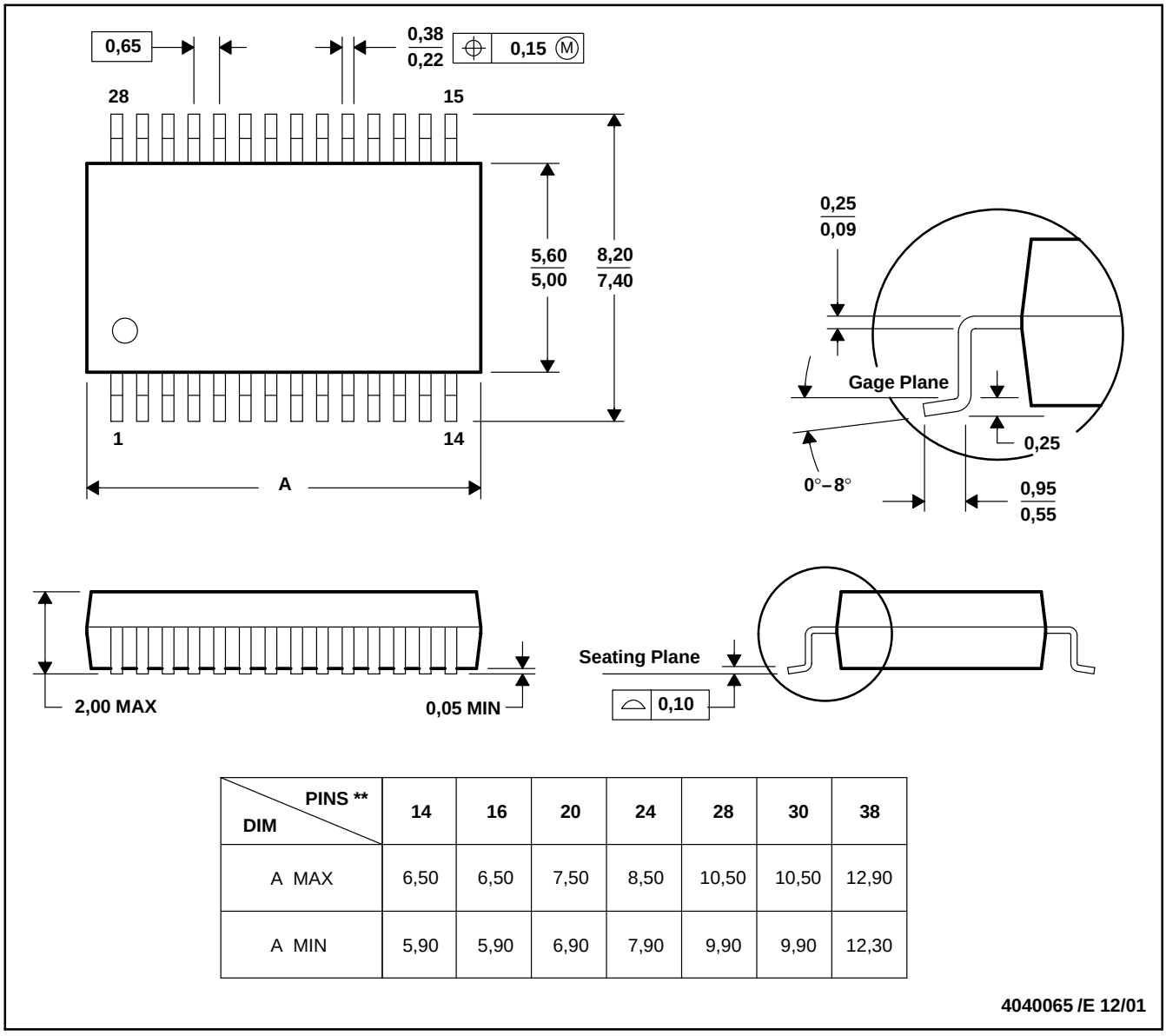


NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Refer to IPC7351 for alternate board design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

MSSO002E – JANUARY 1995 – REVISED DECEMBER 2001

DB (R-PDSO-G)** **PLASTIC SMALL-OUTLINE**

28 PINS SHOWN



DIM \ PINS **	14	16	20	24	28	30	38
A MAX	6,50	6,50	7,50	8,50	10,50	10,50	12,90
A MIN	5,90	5,90	6,90	7,90	9,90	9,90	12,30

4040065 /E 12/01

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. Falls within JEDEC MO-150

重要通知和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做出任何明示或暗示的担保，包括但不限于对适销性、与某特定用途的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他安全、安保法规或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的相关应用。严禁以其他方式对这些资源进行复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。对于因您对这些资源的使用而对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，您将全额赔偿，TI 对此概不负责。

TI 提供的产品受 TI 销售条款)、TI 通用质量指南 或 ti.com 上其他适用条款或 TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。 除非德州仪器 (TI) 明确将某产品指定为定制产品或客户特定产品，否则其产品均为按确定价格收入目录的标准通用器件。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

最后更新日期：2025 年 10 月